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ion is on the order of 45
nt bond; in comparison,
l.

ie hydrophobic, van
ethylene carbons on
layers, this interaction
o maximize the
er the overall surface
s from an alkane chain
ins of this length,
hains can overcome the
m.^{6,7}

in **Figure 1**. (next
as containing 3 parts:
o a noble metal surface,
ethylene groups, (CH₂)_n),
oned above, the sulfur
groups act as the main
ethiols. The head group
ired group can be used
rpe of chemistry.

urface can be created
, hydrophilic (hydroxyl
nt (ethylene glycol head
, azide, carboxyl, amine
to custom design a



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C 1s	O 1s	S 2p	Au 4f
64.5	19.1	1.3	15.1
65.3	20.9	1.2	12.6
55.9	17.3	2.3	24.5
56.2	17.3	2.8	23.7
45.6	12	4.3	38.1
46.2	13.6	4	36.2

decyl)tetra(ethylene glycol); Aldrich
 tic acid

m Table 1 rescaled without the
 comparison of the atomic percentages
 in the solution mixture atomic
 ple 2, the experimental values
 ulated values. The atomic
 ally observed to be lower than
 n by the overlying monolayer. This
 SG₄thiol. The fact that the sulfur
 monolayers is close to the predicted
 layers are disordered (consistent
 ntages) or that there is a high
 in the surface (which has a high
 r vs. the other atoms).

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on Head Group

fannose

NTA, Peptide,

hydrates

I

ptide, PEG_n

COOH, NH₂, OH, SH

1983, 105, 4481. (2)
546. (3) Dubois, L. H.;
437. (4) Bain, C. D.;
, 7164. (5) Bain, C. D.;
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Goeckl, M. S.; Naemi, E.;
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Estroff, L. A.; Kriebel, J. K.;
5, 105, 1103. (12) Chaki, N.;
cs **2002**, 17, 1. (13) Ulman,



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ngstroms

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50 Å

microscopy image of a 24 h SAM on a Au(111) substrate. Image tunnel = 3.0 pA. A) shows several monatomic step edges and resolution: $200 \text{ Å} \times 200 \text{ Å}$; molecular

commonly observed in thiol SAMs show depressed domain rotational domains of the 1-AD SAM systems, domain boundaries associated with differing tilts, rotational and stacking faults.¹¹⁻¹³ **Figure 1 (B)**

1 image with molecular resolution SAM, showing individual hexagonally closed-packed structure of $6.9 \pm 0.4 \text{ Å}$. This lattice is larger than the nearest-neighbor SAMs and can be attributed to 1-AD molecules compared to the (predominantly all-trans) alkyl chains of

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as light) background
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ctadecyl trichlorosilane
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r semiconductor

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SAM is used as the
nce low voltage organic
-assembled multilayers,
nance dielectric layers
sed for initiating
c layers **Figure 3**.⁹



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layer:

Layers for patterning

An active semiconductor layer has to minimize cross talk between devices. Drain and source electrodes need to be separated by at most a few micrometers to meet application requirements.

Printing methods, such as ink-jet and offset printing,¹⁵⁻¹⁷ SAMs are used for selective deposition through patterned wettability or patterning.^{5, 18,19} Patterned SAM layers can be used in photolithography or microcontact patterning of organic semiconductors, as an etch resistant layer to protect the underlying SAM to be patterned. SAM layers have also been used for the selective plating of patterned metal electrodes.²²

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-Cl

33386 (99%)

46963 (97%)

48591 (97%)

30569 (98%)

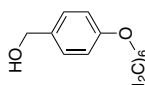
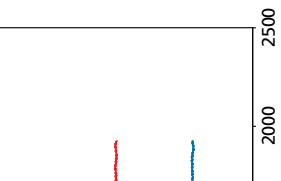
2356 (80%)

90%, **74762** (85+%)

constant are governed by aterials have been successfully ting polymers, ⁴ conjugated	
sigma-aldrich.com/selfassembly.	
	215.00
	215.00
	175.00
ussion of the differences between . No. Z41,033-0. (3) <i>Handbook of</i> ch Prod No. Z54,718-2. (4) Sayre, C.N.; dx. <i>Mater.</i> 1997 , 9, 61.	

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IS(H₂C)₆
h Prod. No. 673560

stic Nanotether™ (red) vs
d by solvent wash. Arrow

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offer unique design capabilities
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with varying degrees of rigidity. A
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r as part of a poly(ethylene glycol)
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ligand. In effect, it becomes a
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OMG 367.00

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Lawrence, Ph.D. from
noteworthy scientists

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Volume (mL)] \times [C \times 10⁻⁶ mol/mL] \times

can convert the mass to a volume

sol. Use a calibrated micropipette for

liquid thiols.

ution. Prepare enough solution for

solution concentration is constant

in preparing mixed thiol solutions,

each thiol separately, then mix

solutions for the final stock solution.

ainers with solvent by squirting ~3 to

of the containers. Repeat 2–3 times

er. Rinse all beakers, tweezers,

experiment with solvent. Label all

volume of solvent into the clean

volume) of thiol, to the solvent.

–10 min to dissolve.

the planned volume of solution

ner.

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